Docket No.: 8733.913.00

Declaration, Power of Attorney and Petition

WE (I) the undersigned inventor(s), hereby declare(s) that:

My residence, post office address and citizenship are as stated below next to my name,

We (I) believe that we are (I am) the original, first, and joint (sole) inventor(s) of the subject matter which is claimed and for which a patent is sought on the invention entitled

FABRICATION METHOD OF POLYCRYSTALLINE SILICON TFT

the specification of which

×	is attached hereto.						
	was filed on						
		as Application No.					
		and amended on	·				
	was filed as PCT international application						
	Number						
	on						
and was amended under PCT Article 19							
	on		(if applicable).				

We (I) hereby state that we (I) have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

We (I) acknowledge the duty to disclose information known to be material to the patentability of this application as defined in Section 1.56 of Title 37 Code of Federal Regulations.

We (I) hereby claim foreign priority benefits under 35 U.S.C. §119(a)-(d) or §365(b) of any foreign application(s) for patent or inventor's certificate, or §365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed. Prior Foreign Application(s)

Application No.	Country	Day/Month/Year	F	Priority Claimed			
10-2003-0035577	KOREA	03 June 2003		Yes		No	
				Yes		No	
			0	Yes		No	
				Yes		No	

We (I) hereby claim provisional application(s) liste			ted	States Code, §119(e) of any United States				
(Applica	(Application Number)			(Filing Date)				
any PCT International applicate each of the claims of this applicant in the manner provided by the	ion icati firs ity a	designating the United States ion is not disclosed in the prict paragraph of 35 U.S.C. §112 as defined in 37 CFR §1.56 w	, lis or U 2, I hic	ny United States application(s), or §365(c) of ted below and, insofar as the subject matter of Jnited States or PCT International application acknowledge the duty to disclose information h became available between the filing date of this application.				
Application Serial No.		Filing Date	П	Status (pending, patented, abandoned)				
powers of substitution and re- Office connected therewith; ar	voca	ation, to prosecute this appli- ve (I) hereby request that all of	cati	p. No. 40,106 as our (my) attorneys, with full on and to transact all business in the Patent espondence regarding this application be sent Law, 1900 K Street, N.W., Washington, D.C.				
statements made on information with the knowledge that willfu	on a l fal Title	nd belief are believed to be t lse statements and the like so e 18 of the United States C	rue; ma ode	(my) own knowledge are true and that all and further that these statements were made de are punishable by fine or imprisonment, or and that such willful false statements may con.				
Sang Hyun KIM		Re	side	ence: Gyeonggi-do, Korea				
NAME OF FIRST INVENTO)R	40	401-503 Seoksu LG village, 415-1 Seoksu-dong					
V4-a			Manan-gu, Anyang-si, Gyeonggi-do, Korea					
75				Citizen of: Republic of Korea				
Signature of Inventor		Po	st C	Office Address: Same as above				